

# Graphene and 2D TMD material optical characterization with scanning probe microscopy

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**Abstract** Two-dimensional (2D) materials distinguish themselves by high specific surface areas and wide tunability in nanophotonics research. As the developing of 2D materials optical and opto-electronic investigations, scanning probe microscopy provides high spatial resolution and strong local field confinement, which can realize the single molecular and atomic level of characterization. Here, we review the nanophotonic and opto-electronic features of both pristine and hybrid 2D materials which are measured by scanning probe microscopy. The conclusion and prospective of scanning probe techniques for the future 2D materials characterization and practical applications are presented.

**Keywords** Two-dimensional materials; Scanning probe microscopy; Nanophotonics; Hybrid structures  
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## 1 Introduction

For two-dimensional (2D) materials, weak interlayer van der Waals bonding allows exfoliation to the monolayer, where the quantum confinement results in optical and electronic features different with that of bulk materials [1, 2]. These varied electronic properties can lead to a broad electromagnetic spectrum [3], and can be applied for non-deviation devices, etc. With a monolayer or few layers, most of 2D materials have strong optical response under incident illumination, and further boom the related opto-electronic applications.

Scanning probe microscopy (SPM) has been applied for 2D material characterization from different aspects. SPM has successfully resolved the molecular structure at the atomic level and measured the topography of 2D materials. The obtained spatial distribution of photon and electron state indicates material opto-electronic properties and contributes to understanding the underlying physical mechanism. On the other hand, the metallic scanning probe can couple to incident light, which leads to extreme localized field enhancement between the tip and material surface at the nanoscale. The responsive optical signal can reveal the molecular information and help in characterizing 2D material optical and structural properties.

In this review, we first introduce the principle and application of different SPM, and then the optical and opto-electronic properties of intrinsic graphene and hybrid TMD materials are summarized. Finally, a perspective of modern characterization methods for future 2D material investigation is given.

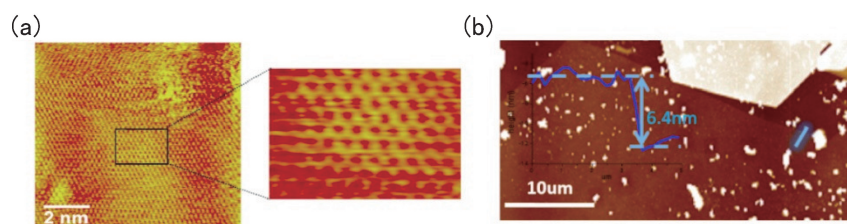
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## 2 The principle and application of SPM family

Scanning tunneling microscopy (STM) and atomic force microscopy (AFM) are two typical kinds of SPM, where the scanning tip with a different tip-sample feedback system can be controlled by either constant height mode or constant interaction mode [4]. The cantilever based tip is used for AFM, while the conducting probe is applied for STM. The nanoscale topography of 2D material flakes can be effectively obtained with AFM and STM measurements. On the other side, the optical and electronic properties of the 2D material can be investigated by using tip enhanced Raman scattering (TERS) and Kelvin probe force microscopy (KPFM), where the material surface potential and electron transfer process can be analyzed.

STM as a typical member of SPM family works with the feedback signal of tunneling current [5]. The wave functions of the scanning tip and sample atoms overlap in a close distance, which drive electrons tunneling through the energy barrier. This electron transfer generates the current between the tip and detected sample surface. In a standard operation, by keeping the current constant and measuring the displacement of the scanner, the surface topography can be obtained in atomic resolution. As shown in Fig. 1(a), the STM image of a thin graphene sheet ( $\sim 1.5$  nm thick) shows a clear honeycomb structure which has a good agreement with theoretical results [6]. Although STM technology is restricted to the conducting material, it has been effectively used to measure the topography of graphene and other 2D materials.

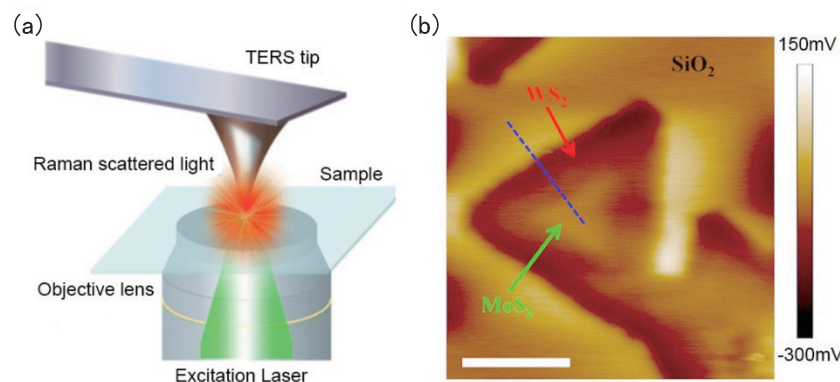


**Figure 1** (a) STM image of a graphene flake. The atomic structure shows a hexagonal pattern [5]. (b) A typical AFM image of MoS<sub>2</sub> flake. The height profile indicates the sheet thickness of 6.4 nm.

In comparison with STM, AFM can be applied to measure all of the samples but with a lower spatial resolution. Instead of directly measuring the atomic force between the tip and sample, the AFM probe is attached to an elastic cantilever which can be used to reflect the diode laser. During the scanning of the sample, the force between the tip and surface can induce subtle bending in the cantilever. The corresponding shift of the reflected laser in the detection screen can describe the sample topography. AFM has been widely applied to measure the topography and height profile of 2D material flakes [7]. As shown in Fig. 1(b), the AFM image reflects the defect and thickness of MoS<sub>2</sub> monolayer as 6.4 nm.

TERS is a technique that combines STM and Raman spectroscopy, which is used to analyze the chemical structure of detected materials [8, 9]. Compared to the conventional surface enhanced Raman spectroscopy (SERS) [10–12], TERS can provide both strong localized field enhancement and high lateral resolution down to 10 nm, which depends on the tip size of the probe [13–16]. As shown in Fig. 2(a), the excitation laser couples to the TERS tip and forms a strong localized field in the detecting area. The scattering signal is collected by the objective lens in the far-field. The high spatial resolution property further develops the optical characterization of 2D materials at the nanoscale.

KPFM is an effective tool to measure the local contact potential difference between the AFM tip and the sample [18, 19]. The surface potential of the sample can be measured with a high spatial resolution, and its electronic properties of the sample surface can be characterized. A typical surface potential image of triangle MoS<sub>2</sub>-WS<sub>2</sub> heterostructure is shown in Fig. 2(b). The work function difference of single-layer MoS<sub>2</sub> and bilayer WS<sub>2</sub> can be clearly observed [19], which can be used to explore the electron transfer process and related optoelectronic features of this heterostructure.



**Figure 2** (a) Schematic of a typical TERS detection in the transmission mode. The localized field was effectively enhanced at LSP resonance. (b) KPFM image of MoS<sub>2</sub>-WS<sub>2</sub> heterostructure on the SiO<sub>2</sub> substrate. Different material work functions lead to the observable surface potential distinction [17].

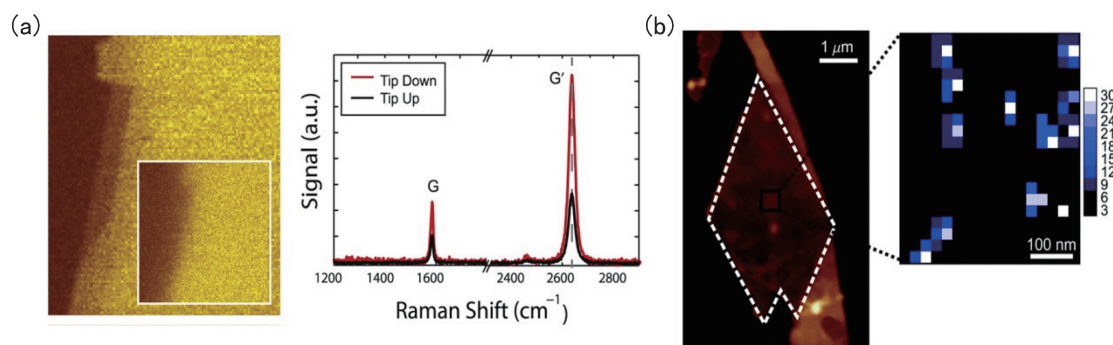
### 3 Pristine and hybrid 2D materials with SPM characterization

Graphene, as a special zero bandgap semi-metal 2D material, has a wide range of electronic and opto-electronic applications. On the other side, transition-metal dichalcogenides (TMD) monolayers are direct bandgap semiconductors with a strong light-matter interaction, which has potential applications for the opto-electronic devices. Both graphene and TMD materials are highly tolerant and chemically stable, thus are suitable candidates for the durable nanophotonic device in the future.

#### 3.1 Pristine graphene

Graphene, as one of the most investigated 2D materials, has unique optical and electrical properties [20]. Scanning probe microscopy paves the way for the high spatial resolution study in graphene [21, 22], and provides an option in revealing its physical mechanism at the nanoscale.

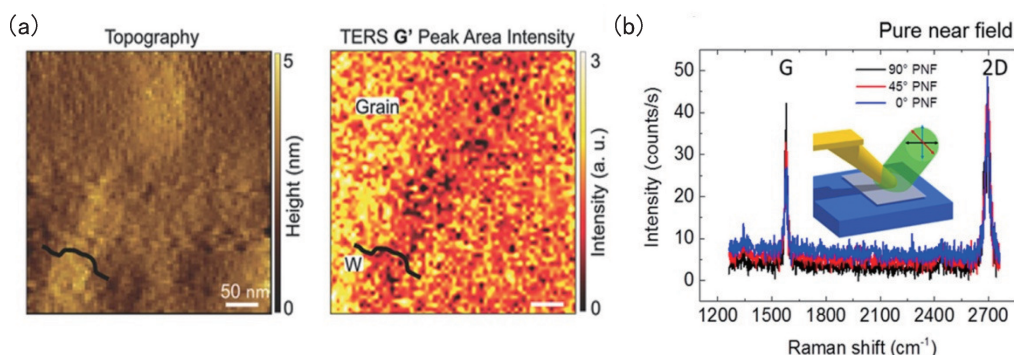
Local strain of graphene relates tightly with the pseudo-magnetic field of the material and further modifies its electronic band structure, which impacts on both photoconductivity and photoresponse of graphene-based devices. Due to the diffraction-limit, the conventional Raman spectroscopy can be hardly used to study the local strain at the nanoscale. However, TERS with the tip size of tens of nanometers overcomes this limit and realizes a local measurement of strain in the graphene monolayer. As shown in Fig. 3(a), the position of strain can be clearly observed from the TERS mapping, and the type of strain is reflected by the G' peak of Raman spectra. This study offers the method of characterizing the strain of graphene with a high spatial resolution, which contributes to the investigation of graphene quantum properties, and also the design of graphene-based opto-electronic devices.



**Figure 3** (a) Left: TERS mapping of graphene G' band. Right: Raman scattering spectra of tip up/down two situations [23]. (b) Tip Enhanced Raman Mapping (TERM) of a monolayer graphene sheet. The Raman D-peak intensity image shows point defects [24].

Defects in graphene have aroused wide interest for their significant impact on the device performance [22, 23]. The conventional confocal microscopy has been widely utilized to study defects [25–27]. However it suffers the weakness in estimating the defect size, especially for the localized individual defect. SPM with the high spatial resolution provides an effective way to measure the point to point distance [28]. It was reported that the individual defect in graphene was successfully measured by TERS, as shown in Fig. 3(b). From the spectrum, we can see the value of  $I(D)/I(G)$  has the positive correlation with the occurrence of defects. Both inter-defect distance and size of individual defects can be determined [29], which avoid potentially negative influence on the development of graphene-based devices. On the other side, these defects can also play the role of tuning graphene optical properties [30, 31]. In comparison with regular methods, i. e. the impurity introduction and bias doping, the defect tuning technique has the advantage in accuracy control at the nanoscale, which broadens the utilization of defects in graphene for the future opto-electronic device.

Besides the defect of graphene, other intrinsic discontinuities can also influence the material optical and electrical properties [32, 33]. Wrinkles, for example, can affect the graphene electron transport and limit the photoconductivity performance. In order to investigate the graphene wrinkles, TERS was introduced to characterize the optical and chemical properties of these discontinuities with a high resolution as shown in Fig. 4(a), where the  $G'$  peak experienced a conspicuous intensity decreasing at the location of wrinkles [34]. This TERS study helps in understanding the structure curvature effect on graphene, further providing the method to avoid the potential influence of wrinkles on the future device application.



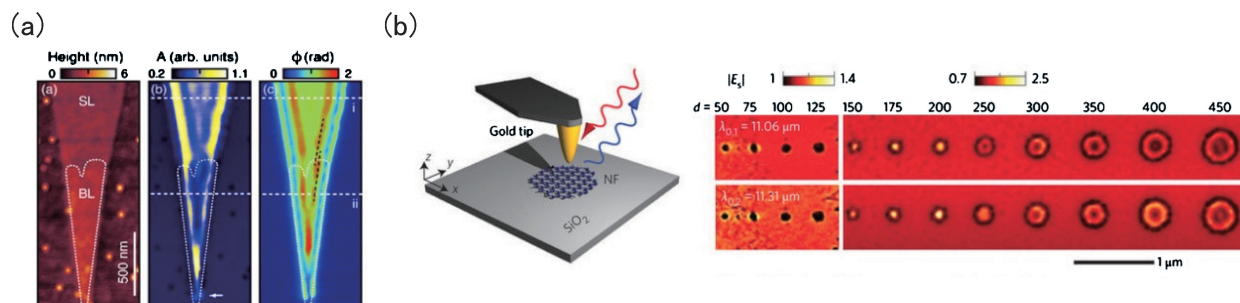
**Figure 4** (a) Left: STM image of graphene wrinkle structure. Right: Corresponding TERS image of  $G'$  peak intensity [34]. (b) TERS spectra of graphene in different tilted geometry in the near field [35].

In order to further investigate the selection rule, polarization-dependent TERS was performed on graphene, where corresponding peak intensities of  $G$  and  $G'$  band changed enormously in the near field (Fig. 4(b)) [35, 36]. This result contradicts to the selection rule of the conventional Raman scattering [37], and suggests a quantum process of photon tunneling. It deepens the understanding of the TERS mechanism and broadens potential opto-electronic utilization of graphene as the substrate for the TERS measurement [38].

Graphene has also been used to investigate the plasmonic resonance in the THz region. The grain boundary and surface defect mentioned above play an important role in the scattering of surface plasmon polaritons (SPPs). To characterize the SPPs propagation in the graphene monolayer, the AFM tip was used to induce the SPPs excitation [39–42], and the tip-scattered near-field optical signal could be measured by the HgCdTe detector in the infrared region. As shown in Fig. 5(a), the graphene SPPs amplitude and phase information were collected by the modified AFM, from which we could tell the height of the graphene changed from monolayer to bilayer. In comparison with the monolayer, the SPPs propagation in the bilayer graphene has decreased amplitude and smaller excited wavelength [36, 37]. This study provides a comprehensive way of detecting and tuning the electronic structure of graphene at the nanoscale, and has potential in graphene-based plasmonic applications [43].

Similar to the intrinsic defect of graphene, edge effects can also impact on the plasmon behavior [46].





**Figure 5** (a) Height, amplitude and phase maps of graphene nanoribbon [44]. (b) Schematic and results of real-space mapping graphene nanodisk plasmon modes experiment [45].

The generated plasmon resonance mode provides an effective confinement and enhancement of the localized field. In order to study these resonance modes, AFM-based near-field optical microscopy was applied, where the probe tip could be used to enhance the localized electromagnetic field. From Fig. 5(b), we can see that the plasmon near-field resonance changes with the diameter of the graphene nanodisk increasing from 50 to 450 nm, with its maximum intensity obtained at the diameter of 200 nm, and edge plasmon enhancement appears with the nanodisk diameter of 75 nm. This size difference indicates resonance modes distinction between the graphene sheet and edge, and opens up the investigation for edge modes of graphene by the real-space imaging technique.

### 3.2 Hybrid TMD materials

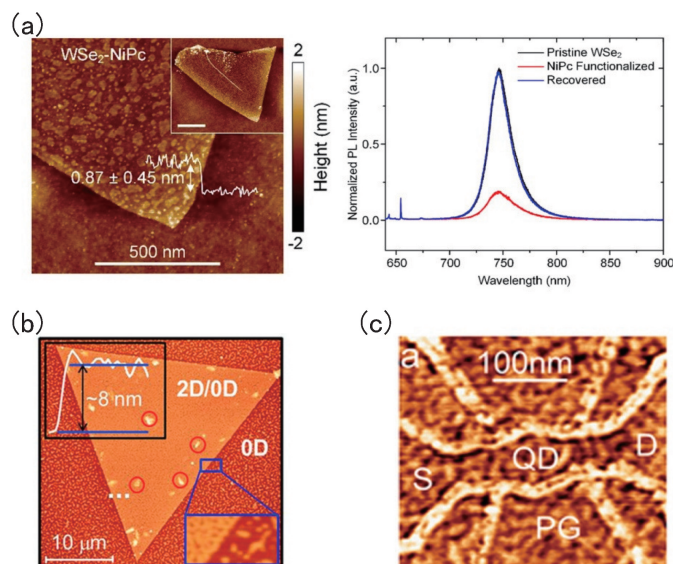
Compared to intrinsic graphene, hybrid 2D materials have a wider tunability in optical and electrical properties by introducing nanostructures with strong and functional tuning ability. By coupling with materials in different dimensions varying from 0D to 2D, hybrid structures show distinct and diversiform optical and opto-electronic properties for the device application.

Molecules as typical 0D materials, can bring various optical features and enrich hybrid structures properties [47–50]. For example, NiPc molecules were used to manipulate the PL response of  $\text{WSe}_2$  monolayer by reducing their potential locations between the  $\text{WSe}_2$  conduction and valence bands. From the AFM image of Fig. 6(a), the  $\text{WSe}_2$  monolayer was functionalized by NiPc molecules [51]. Compared with the PL spectrum of pristine  $\text{WSe}_2$ , the  $\text{WSe}_2$ -NiPc hybrid presents a PL intensity decrease, which consists with the theoretical estimation. This PL tuning is reversible when NiPc molecules are rinsed from the  $\text{WSe}_2$  monolayer, which indicates an active manipulation in TMD-based opto-electronic devices at the molecular level.

On the other side, semiconductor quantum dots (QDs) distinguish themselves by miscellaneousness and wide size-tunability [52, 53]. Hybrid structures of TMD materials and quantum dots can tailor the optical performance for the opto-electronic application [54]. As shown in Fig. 6(b), the  $\text{WS}_2$  flake spin-coated by CdSe/ZnS QDs can be imaged by the AFM. In order to study the electron transfer in this hybrid structure, the transient absorption spectrum was measured. The result shows that electrons of QDs and holes from  $\text{WS}_2$  can generate indirect excitons, which leads to an effective exciton coupling, and contributes to the design of hybrid 0D/2D heterostructures for the sensor device [55].

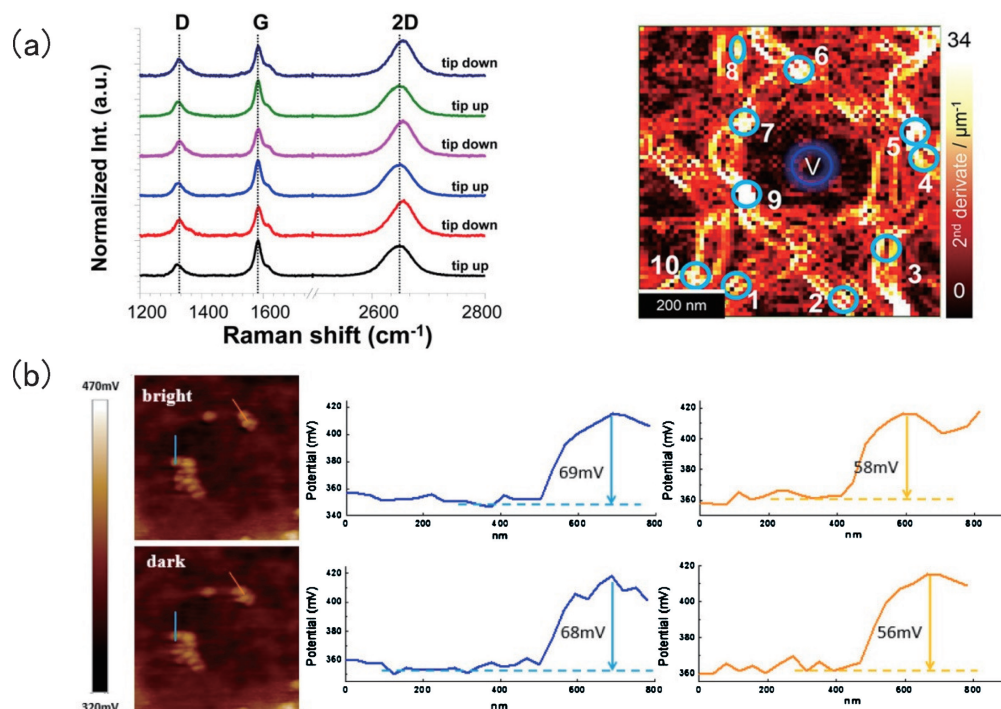
Compared to widely utilized semiconductor QDs, graphene QDs have a broad excitonic absorption band [59, 60], which satisfies the need for photovoltaic devices [61]. By applying the tip-induced method, the formative graphene QDs can confine electrons in the structure gap, and result in the enhancement of the local field. The spatial energy dependence can be probed by the tip-induced QD as shown in Fig. 6(c), which verifies electron behaviors of graphene QDs. This tip potential probing method helps in manipulating excitonic energy of graphene QDs, and broadens the applications of QDs in graphene-based opto-electronic devices [62, 63].

The electronic structure of graphene-metal hybrids was widely studied for opto-electronic applications [64, 65]. TERS was used to measure the optical response of graphene-Au nanoparticle (NP) hybrid



**Figure 6** (a) Left: AFM image of Nickle Pc (NiPc) molecules adsorbed on the WSe<sub>2</sub> single layer; Right: PL intensity spectra of pristine WSe<sub>2</sub>, WSe<sub>2</sub>-NiPc and WSe<sub>2</sub> nanosheets after rinsing NiPc [56]. (b) AFM images of WS<sub>2</sub> nanosheet after being spin-coated by CdSe/ZnS nanodots. The height profile indicates the rising thickness of nanosheet from 0.7 to 8 nm after coating [57]. (c) Topography of a tip-induced graphene quantum dot [58].

structure, as shown in the left image of Fig. 7(a). From the TERS spectrum, we can see that electrons are effectively restrained by Au NPs on the graphene [66]. Compared with the graphene-metal hybrid, TMD-metal hybrids show a large tunability in opto-electronic properties. The TERS mapping of a MoS<sub>2</sub> envelope on Au nanotriangle structures shows that the brightest spots correspond to the strongest strain in the bending of MoS<sub>2</sub> monolayer (right image in Fig. 7(a)) [67], which indicates the application of strain-tuning in TMD-metal hybrids.

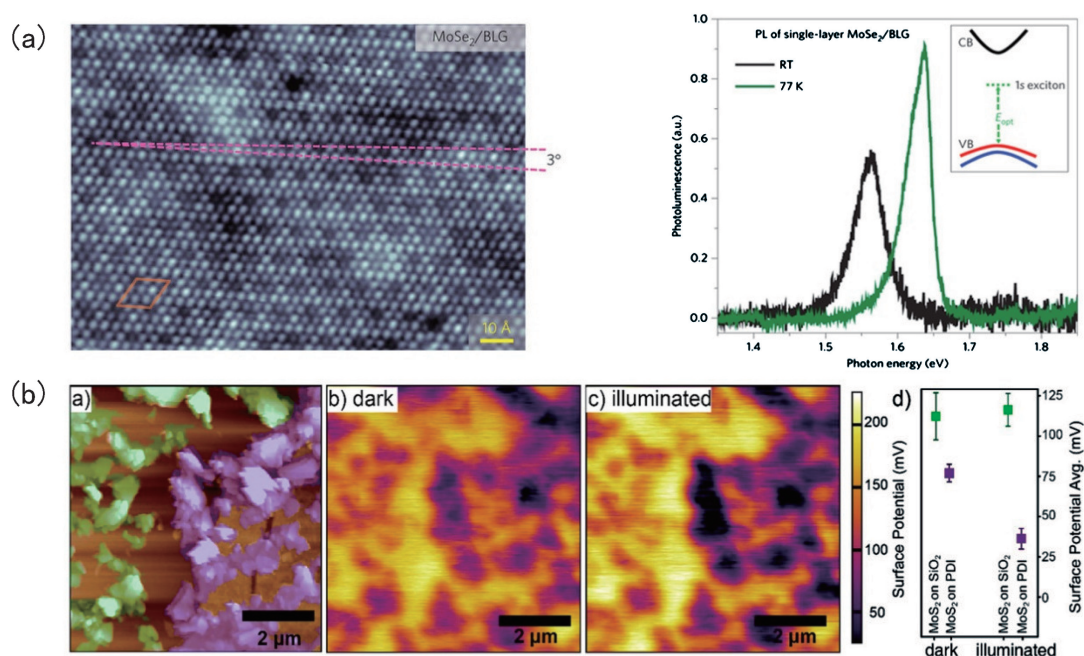


**Figure 7** (a) Left: TERS spectra of graphene-Au NPs with and without tip away from Au NPs [66]. Right: TERS image of second order derivative points in MoS<sub>2</sub>/Au nanotriangle hybrids [67]. (b) KPFM surface potential detection of Au-MoS<sub>2</sub> hybrid material. The thickness of MoS<sub>2</sub> is 18.4 nm [68].

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By coupling with the metallic nanostructure, the PL of 2D materials can be manipulated. To investigate the effect of the electron injection process on the PL intensity, KPFM measurement was performed to obtain the surface potential of nanoflakes under different light illuminations (Fig. 7(b)) [68]. Together with PL results, it can be seen that the illumination affects less in the thinner MoS<sub>2</sub> flake than in the thicker one, which indicates that the electron transfer process from MoS<sub>2</sub> to Au NP dominates in the thinner flake, and results in the PL quenching. This study contributes to realizing PL tuning in metal-MoS<sub>2</sub> hybrids by manipulating the thickness of the nanosheet, thus helping in developing TMD-based opto-electronic devices [69].

Excitonic effects of TMD heterostructures have aroused attention for their wide optical applications [70, 71]. The topography of MoSe<sub>2</sub> on the bilayerd graphene (BLG) heterostructure surface is shown in Fig. 8(a), where the moire pattern of MoSe<sub>2</sub> monolayer misfits the lattice of MoSe<sub>2</sub>/BLG. By measuring the PL of MoSe<sub>2</sub>/BLG heterostructure at room temperature and 77 K [72], the 0.08 eV peak-shift was recorded, which indicated the rise of optical bandgap in the MoSe<sub>2</sub> monolayer induced by the BLG substrate. This experiment reveals the temperature-dependent peculiarity of exciton-hole excitation binding energy between the MoSe<sub>2</sub> and BLG.



**Figure 8** (a) Left: Topography of single-layer MoSe<sub>2</sub> on bilayer graphene. Distinction of MoSe<sub>2</sub> lattice and the Moire pattern has an angle of 3 degree. Right: PL measurements of MoSe<sub>2</sub>/BLG monolayer at 77 K and room temperature, respectively [73]. (b) KPFM measurements of MoS<sub>2</sub> nanosheets on both glass and Dihexanoic acid-perylene-diimide (DHA-PDI) substrates, respectively [74].

TMD-organic heterojunctions, on the other side, are suitable candidates for photovoltaic applications because of their high tolerance and low preparation cost. The surface potential of MoS<sub>2</sub>/DHA-PDI heterostructure was investigated by the KPFM [74]. As shown in Fig. 8(b), different heterostructures of MoS<sub>2</sub>/PDI and MoS<sub>2</sub>/SiO<sub>2</sub> were measured in the same square region with the size of 2  $\mu$ m. The result shows that MoS<sub>2</sub>/PDI has a decrease in the surface potential under illumination, while the MoS<sub>2</sub>/SiO<sub>2</sub> heterostructure nearly remains the same, which suggests an efficient electron injection from MoS<sub>2</sub> to PDI under the incident illumination [75].

## 4 Conclusion and perspective

In the investigation of nanophotonic features of graphene and TMD materials, SPM plays an important role in providing high spatial resolution information of the nanostructure. For pristine graphene, its optical

and opto-electronic features are impacted by the edge effect and other intrinsic discontinuities, such as defects and wrinkles, which can be characterized and manipulated by SPM. For hybrid 2D materials, the stacked heterostructure can obtain a broad tuning ability compared with the intrinsic 2D monolayer. The hybrids in different dimensions were introduced and compared for the future opto-electronic device application, which were characterized by various SPM with high spatial resolution and enhanced electromagnetic field at the nanoscale.

For the future research, advanced techniques are in need for a deeper looking of insight physics of 2D materials. Function integrations of SPM and other optical characterization methods are required for *in-situ* optical measurements in some extreme conditions. Besides TERS, the combination of PL and ultrafast lasers with STM can realize TEPL and THz-STM techniques, respectively [76, 77]. Other opto-electronic characterizations such as photocurrent and cathodoluminescence are candidates in scanning probe measurements of 2D materials [78]. These characterization methods have potential applications for the strong coupling of light-matter interaction, and can lead to an unprecedented future for the 2D material based opto-electronic devices.

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